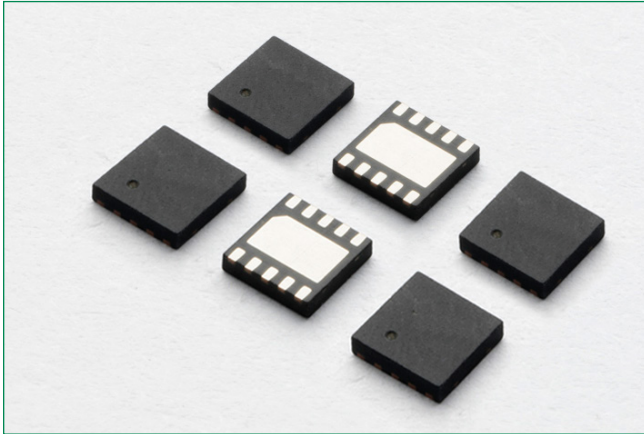


SP3304N

Series 3.3V 20A Diode Array



Additional Information



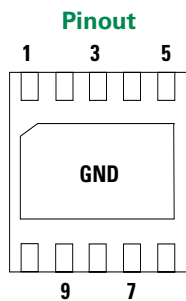
Resources



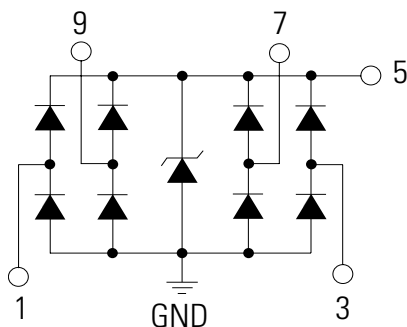
Accessories



Samples



Functional Block Diagram



Description

The SP3304N integrates 4 channels of low capacitance diodes with an additional zener diode to protect sensitive I/O pins against lightning induced surge events and ESD. This robust device can safely absorb up to 20A per IEC 61000-4-5 2nd Edition ($t_P=8/20\mu s$) without performance degradation and a minimum $\pm 30kV$ ESD per IEC 61000-4-2. The low loading capacitance makes the SP3304N ideal for protecting high-speed signal pins.

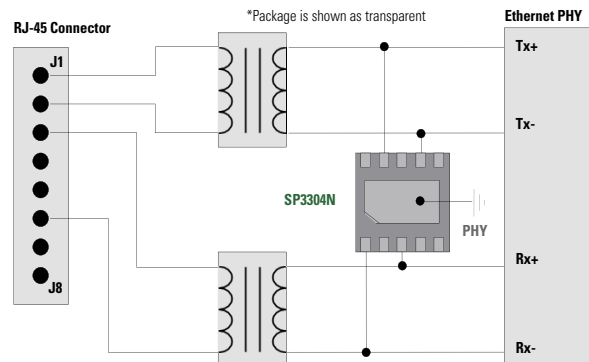
Features & Benefits

- RoHS compliant, lead-free and halogen-free
- ESD, IEC 61000-4-2, $\pm 30kV$ contact, $\pm 30kV$ air
- EFT, IEC 61000-4-4, 40A ($t_P=5/50ns$)
- Lightning, IEC 61000-4-5 2nd Edition, 20A ($t_P=8/20\mu s$)
- Low capacitance of 3.5pF (TYP) per I/O
- Low leakage current of $1\mu A$ (MAX) at 3.3V
- Moisture Sensitivity Level (MSL Level-1)

Applications

- 10/100/1000 Ethernet Interfaces
- Customer Premise Equipment (CPE)
- VoIP Phones
- Set Top Boxes
- PBX Systems
- Small Cells

Application Example



Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

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Absolute Maximum Ratings

Symbol	Parameter	Value	Units
I_{PP}	Peak Current ($t_p=8/20\mu s$)	20.0	A
P_{PK}	Peak Pulse Power ($t_p=8/20\mu s$)	300	W
T_{OP}	Operating Temperature	-40 to 125	°C
T_{STOR}	Storage Temperature	-55 to 150	°C

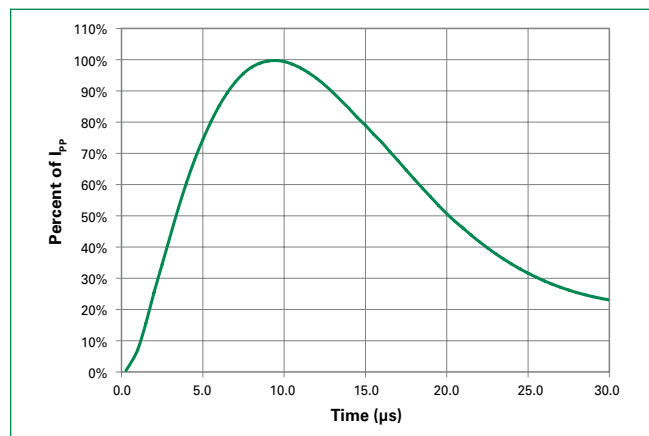
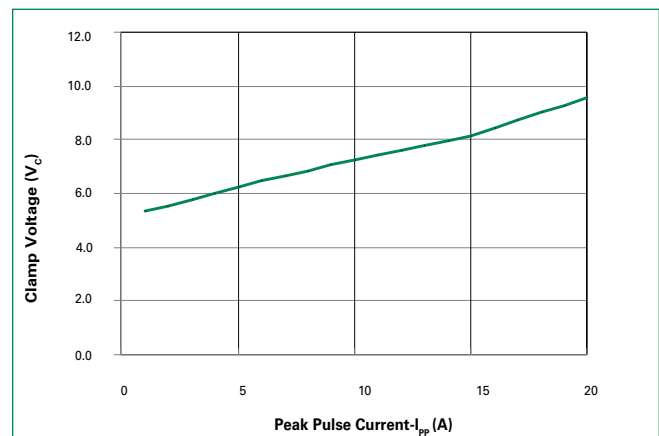
Caution: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Electrical Characteristics (TOP=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}				3.3	V
Punch Through Voltage	V_{PT}	$I_{PT}=5\mu A$	3.5			V
Snap Back Voltage	V_{SB}	$I_{SB}=50mA$	2.8			V
Reverse Leakage Current	I_{LEAK}	$V_R=3.3V$, I/O to GND		0.5	1.0	μA
Clamp Voltage ¹	V_C	$I_{PP}=1A$, $t_p=8/20\mu s$, Fwd			6.0	V
		$I_{PP}=5A$, $t_p=8/20\mu s$, Fwd			7.0	V
		$I_{PP}=10A$, $t_p=8/20\mu s$, Fwd			8.0	V
		$I_{PP}=20A$, $t_p=8/20\mu s$, Fwd			11.5	V
Dynamic Resistance ²	R_{DYN}	TLP, $t_p=100ns$, I/O to GND		0.25		W
ESD Withstand Voltage ¹	V_{ESD}	IEC61000-4-2 (Contact)	± 30			kV
		IEC61000-4-2 (Air)	± 30			kV
Diode Capacitance ¹	$C_{I/O-GND}$	Reverse Bias=0V, f=1MHz		3.5	5.0	pF
Diode Capacitance ¹	$C_{I/O-I/O}$	Reverse Bias=0V, f=1MHz		2.0		pF

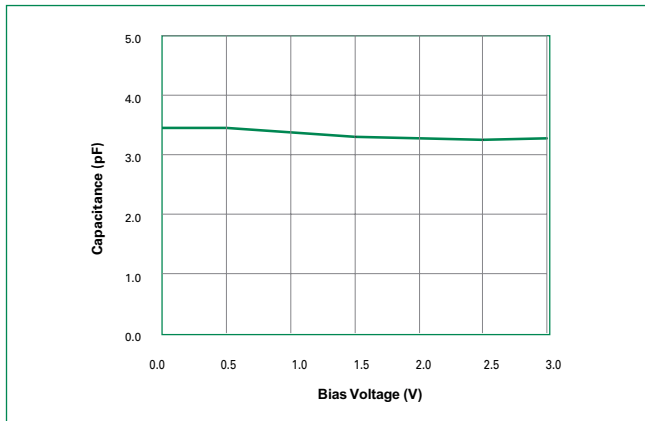
Note: ¹ Parameter is guaranteed by design and/or device characterization.

² Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window $t_1=70ns$ to $t_2=90ns$

Pulse Waveform**Clamping Voltage vs. IPP**

SP3304N

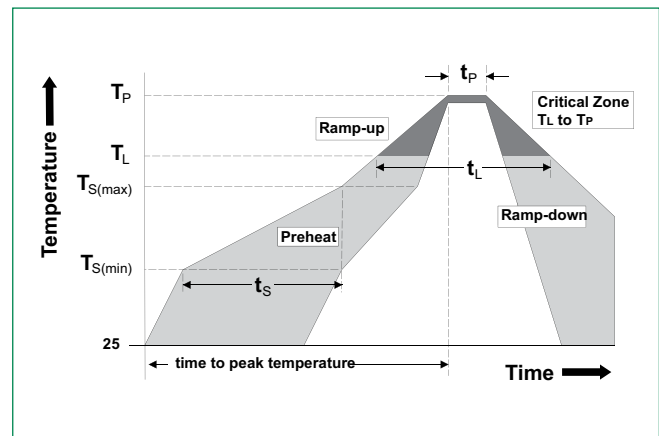
Series 3.3V 20A Diode Array

Capacitance vs. Bias**Ordering Information**

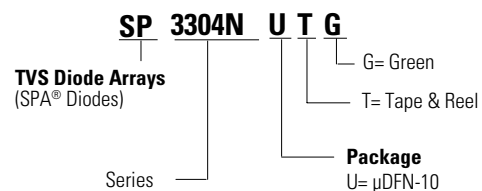
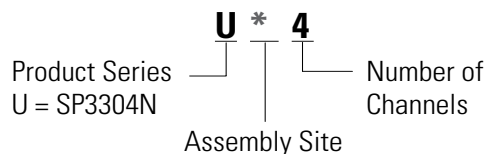
Part Number	Package	Min. Order Qty.
SP3304NUTG	μDFN-10	3000

Soldering Parameters

Reflow Condition	Pb – Free assembly	
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus) Temp (T_L) to peak	3°C/second max	
$T_{s(max)}$ to T_L - Ramp-up Rate	3°C/second max	
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)	260 ^{+0/-5} °C	
Time within 5°C of actual peak Temperature (t_p)	20 – 40 seconds	
Ramp-down Rate	6°C/second max	
Time 25°C to peak Temperature (T_p)	8 minutes Max.	
Do not exceed	260°C	

**Product Characteristics**

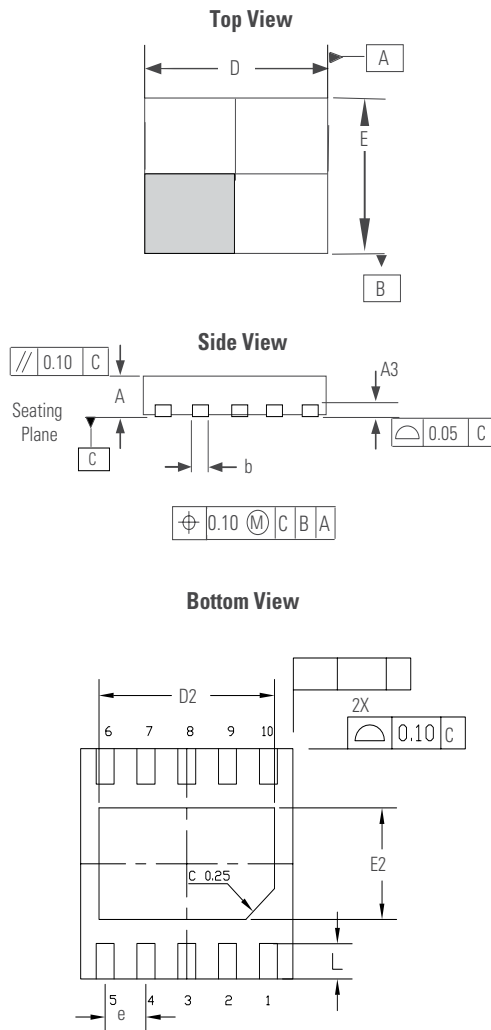
Lead Plating	Pre-Plated Frame
Lead Material	Copper Alloy
Substrate Material	Silicon
Body Material	Molded Epoxy
Flammability	UL Recognized compound meeting flammability rating V-0

Part Numbering System**Part Marking System**

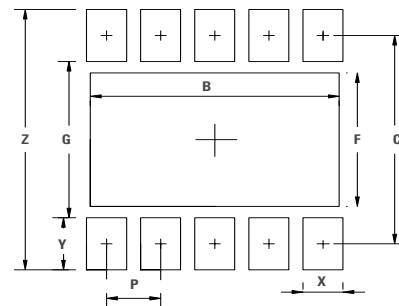
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Package Dimensions — μ DFN-10

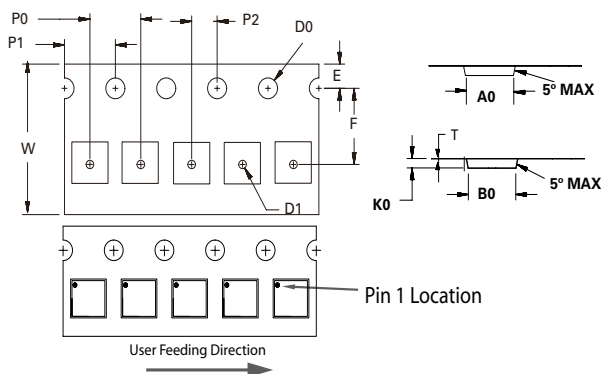


Package	μ DFN-10 (2.6x2.6mm)					
JEDEC	MO-229					
Symbol	Millimeters			Inches		
	Min	Nom	Max	Min	Nom	Max
A	0.45	0.50	0.55	0.018	0.020	0.022
A3	0.130 Ref			0.005 Ref		
b	0.17	0.22	0.27	0.006	0.008	0.010
D	2.50	2.60	2.70	0.097	0.101	0.105
D2	2.10	2.15	2.20	0.081	0.083	0.085
E	2.50	2.60	2.70	0.097	0.101	0.105
E2	1.21	1.26	1.31	0.046	0.049	0.051
e	0.50 BSC			0.020 BSC		
L	0.35	0.40	0.45	0.014	0.016	0.018

Recommended Solder Pads μ DFN-10L 2.6x2.6mm

Symbol	Dimension	
	Millimeters	Inches
B	2.30	0.091
C	2.20	0.087
F	1.41	0.056
G	1.65	0.065
P	0.50	0.020
X	0.37	0.015
Y	0.55	0.022
Z	2.75	0.108

Embossed Carrier Tape & Reel Specification — μ DFN-10 (2.6x2.6mm)



Symbol	Millimeters
A0	2.82 ± 0.05
B0	2.82 ± 0.05
D0	Ø1.50 + 0.10
D1	Ø 0.50 + 0.05
E	1.75 ± 0.10
F	3.50 ± 0.05
K0	0.76 ± 0.05
P0	4.00 ± 0.10
P1	4.00 ± 0.10
P2	2.00 ± 0.05
T	0.25 ± 0.02
W	8.00 + 0.30 /- 0.10

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